



#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	6mΩ @ V <sub>GS</sub> = 10V	80A
60V	8.5mΩ @ V <sub>GS</sub> = 4.5V	70A

### **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- Synchronous Rectifier
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

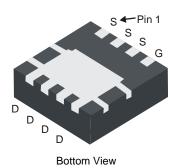
## **Features and Benefits**

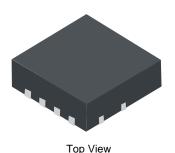
- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area by enabling smaller end products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

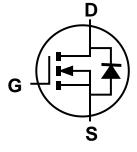
#### **Mechanical Data**

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

#### POWERDI®3333-8







**Equivalent Circuit** 

## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT6007LFG-7	POWERDI <sup>®</sup> 3333-8	2,000/Tape & Reel
DMT6007LFG-13	POWERDI <sup>®</sup> 3333-8	3,000/Tape & Reel

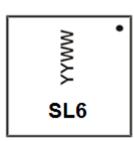
Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



## **Marking Information**

#### POWERDI®3333-8



SL6 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 14 = 2014) WW = Week Code (01 ~ 53)

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
TA:		I <sub>D</sub>	15 12	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	80 65	А
Maximum Continuous Body Diode Forward Current (Note 6	I <sub>S</sub>	80	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	80	Α	
Avalanche Current, L=0.1mH	I <sub>AS</sub>	20	А	
Avalanche Energy, L=0.1mH	E <sub>AS</sub>	20	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		$P_{D}$	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	55	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		$P_{D}$	62.5	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0</sub> JC	2	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

Notes:

<sup>5.</sup> R<sub>BJA</sub> is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. R<sub>BJC</sub> is guaranteed by design while R<sub>BJA</sub> is determined by the user's board design.

<sup>6.</sup> Short duration pulse test used to minimize self-heating effect.

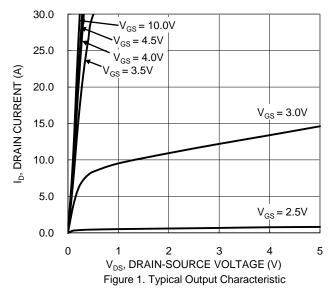


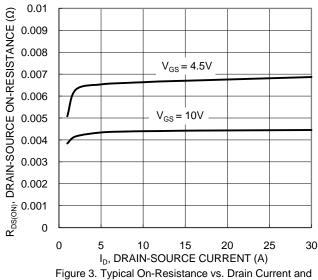
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	_	2	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	4.5	6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	6.5	8.5	11122	$V_{GS} = 4.5V, I_D = 15A$	
Forward Transconductance	G <sub>FS</sub>	_	100	_	S	$V_{DS} = 5V, I_{D} = 20A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	_	2090	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	Crss	_	38.5	_			
Gate Resistance	Rq	_	0.59	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	19.3	_		V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qq	_	41.3	_			
Gate-Source Charge	Qgs	_	6.0	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	8.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.7	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	4.3	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	23.4	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	9.7	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	35.4	_	ns	1 000 11/11 4000/	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	38.2	_	nC	I <sub>F</sub> = 20A, di/dt = 100A/μs	

Note: 7. Guaranteed by design. Not subject to product testing.







Gate Voltage

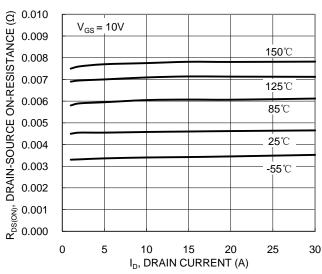
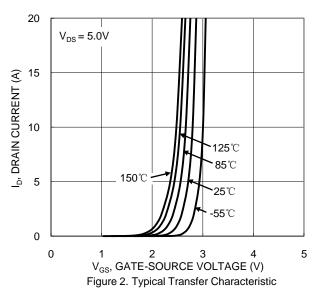
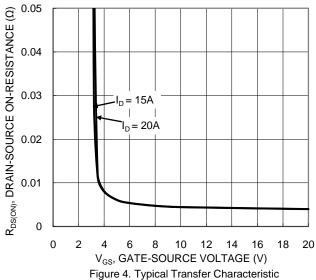


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





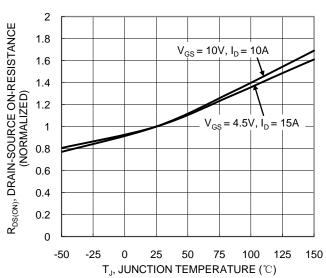


Figure 6. On-Resistance Variation with Temperature



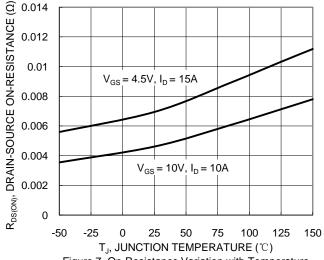


Figure 7. On-Resistance Variation with Temperature

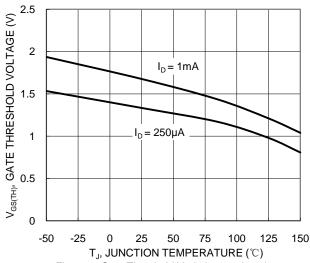
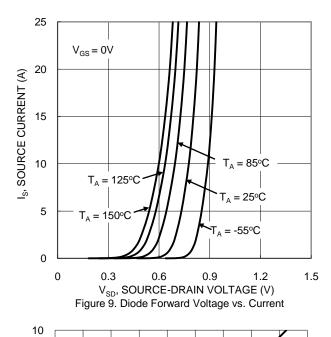
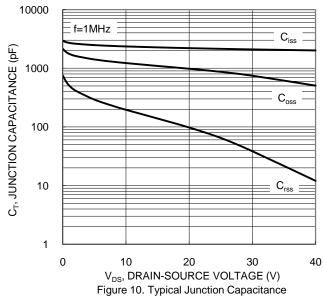


Figure 8. Gate Threshold Variation vs. Junction Temperature





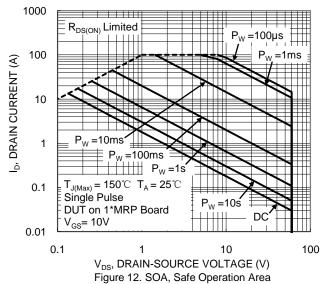
45

 $V_{DS} = 30V, I_{D} = 20A$ 

30

35

40



10

15

20

 $Q_g$  (nC)

Figure 11. Gate Charge

25

5

9

8

7

5 4

3

2

1

0

0

 $V_{GS}(V)$ 6



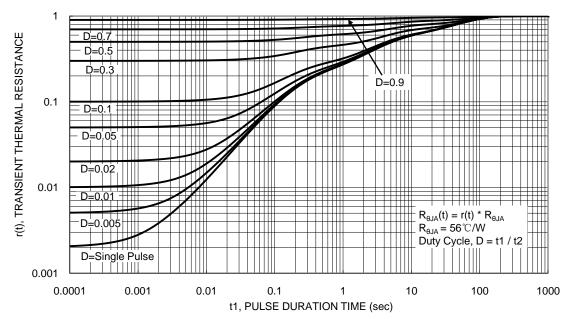


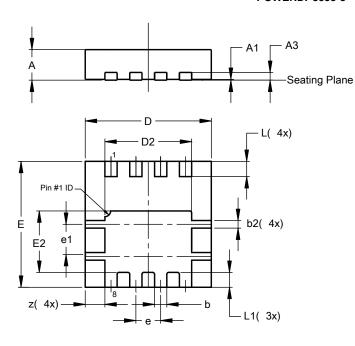
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### POWERDI®3333-8

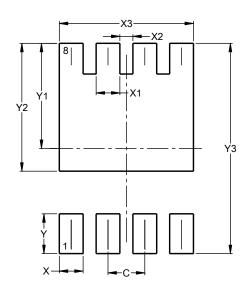


POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	1	-	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	_	_	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### POWERDI®3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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